SILICON POWER TRANSISTOR 2SC4554

NPN SILICON EPITAXIAL TRANSISTOR FOR SWITCHING

The 2SC4554 is a power transistor designed especially for low collector saturation voltage and features large current switching at a low power dissipation.

In addition, a high hre enables alleviation of the driver load.

FEATURES

NEC

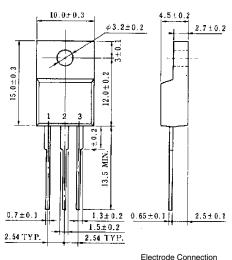
- High hFE and low VCE(sat): hFE \cong 800 (VCE = 2 V, IC = 5 A) VCE(sat) \cong 0.12 V (IC = 5 A, IB = 0.05 A)
- On-chip C to E damper diode
- Mold package that does not require an insulating board or insulation bushing

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit	
Collector to base voltage	Vсво	100	V	
Collector to emitter voltage	VCEO	100	V	
Emitter to base voltage	Vebo	7.0	V	
Collector current (DC)	IC(DC)	±15	А	
Collector current (pulse)	IC(pulse)*	±22	А	
Base current (DC)	B(DC)	4.0	А	
Total power dissipation	P⊤ (Tc = 25°C)	35	W	
Total power dissipation	P⊤ (Ta = 25°C)	2.0	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	–55 to +150	°C	

* PW \leq 10 ms, duty cycle \leq 50%

PACKAGE DRAWING (UNIT: mm)



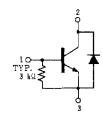


Electrode Connection
1. Base

2. Collector

3. Emitter

EQUIVALENT CIRCUIT

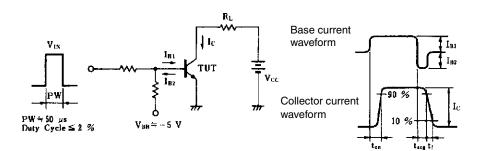


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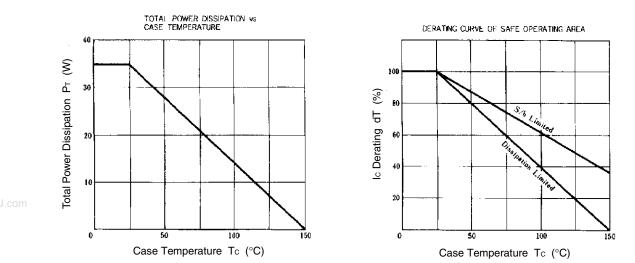
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	V _{CB} = 100 V, I _E = 0			10	μA
Emitter cutoff current	Іево	Vев = 5.0 V, Iс = 0			17	mA
DC current gain	h _{FE1}	Vce = 2.0 V, Ic = 5.0 A	450	800	2,000	
DC current gain	hfe2	Vce = 2.0 V, Ic = 10 A	150			
Collector saturation voltage	V _{CE(sat)1}	Ic = 5.0 A, Iв = 100 mA			0.25	V
Collector saturation voltage	V _{CE(sat)2}	Ic = 5.0 A, Iв = 50 mA		0.12	0.3	V
Collector saturation voltage	V _{CE(sat)3}	Ic = 10 A, Iв = 200 mA			0.4	V
Collector saturation voltage	V _{CE(sat)4}	Ic = 10 A, Iв = 100 mA			0.75	V
Base saturation voltage	V _{BE(sat)}	Ic = 10 A, Iв = 100 mA			1.2	V
Gain bandwidth product	f⊤	Vce = 5.0 V, Ic = 1.0 A		100		MHz
Collector capacitance	Cob	V _{CB} = 10 V, I _E = 0, f = 1 MHz		210		pF
Turn-on time	ton	$\begin{split} I_{C} &= 8.0 \text{ A}, \text{ R}_{L} = 2.0 \Omega, \\ I_{B1} &= -I_{B2} = 80 \text{ mA}, \text{ V}_{CC} \cong 16 \text{ V} \\ \text{Refer to the test circuit.} \end{split}$		0.5		μs
Storage time	t _{stg}			2.0		μs
Fall time	tr			0.5		μs
Diode forward voltage	VDF	IDF = 10 A		1.6		V
	Collector cutoff current Emitter cutoff current DC current gain DC current gain Collector saturation voltage Collector saturation voltage Collector saturation voltage Gain bandwidth product Collector capacitance Turn-on time Storage time Fall time	Collector cutoff currentIcBoEmitter cutoff currentIEBODC current gainhFE1DC current gainhFE2Collector saturation voltageVcE(sat)1Collector saturation voltageVcE(sat)2Collector saturation voltageVcE(sat)3Collector saturation voltageVcE(sat)4Base saturation voltageVBE(sat)Gain bandwidth productfrCollector capacitanceCobTurn-on timetonStorage timetstgFall timetr	Collector cutoff currentIcBOVcB = 100 V, IE = 0Emitter cutoff currentIEBOVEB = 5.0 V, Ic = 0DC current gainhFE1VcE = 2.0 V, Ic = 5.0 ADC current gainhFE2VcE = 2.0 V, Ic = 10 ACollector saturation voltageVcE(sat)1Ic = 5.0 A, IB = 100 mACollector saturation voltageVcE(sat)2Ic = 5.0 A, IB = 50 mACollector saturation voltageVcE(sat)3Ic = 10 A, IB = 200 mACollector saturation voltageVcE(sat)4Ic = 10 A, IB = 100 mACollector saturation voltageVcE(sat)3Ic = 10 A, IB = 100 mACollector saturation voltageVcE(sat)4Ic = 10 A, IB = 100 mAGain bandwidth productfrVcE = 5.0 V, Ic = 1.0 ACollector capacitanceCobVcB = 10 V, IE = 0, f = 1 MHzTurn-on timetonIc = 8.0 A, RL = 2.0 Ω, IB1 = -IB2 = 80 mA, Vcc = 16 V Refer to the test circuit.	Collector cutoff currentIcBoVcB = 100 V, IE = 0Emitter cutoff currentIEBOVEB = 5.0 V, Ic = 0DC current gainhFE1VcE = 2.0 V, Ic = 5.0 A450DC current gainhFE2VcE = 2.0 V, Ic = 10 A150Collector saturation voltageVcE(sat)1Ic = 5.0 A, IB = 100 mA150Collector saturation voltageVcE(sat)2Ic = 5.0 A, IB = 50 mA16Collector saturation voltageVcE(sat)2Ic = 10 A, IB = 200 mA16Collector saturation voltageVcE(sat)4Ic = 10 A, IB = 100 mA16Gain bandwidth productfrVcE(sat)4Ic = 10 A, IB = 100 mA16Gain bandwidth productfrVcE = 5.0 V, Ic = 1.0 A16Turn-on timetonIc = 8.0 A, RL = 2.0 Q, IB1 = -IB2 = 80 mA, Vcc ≅ 16 V Refer to the test circuit.16Fall timetrtstgRefer to the test circuit.16	Collector cutoff currentIcBOVcB = 100 V, IE = 0IcBOEmitter cutoff currentIEBOVEB = 5.0 V, Ic = 0Image: collector current gainImage: collector current gain <td< td=""><td>Collector cutoff current IcBO VcB = 100 V, IE = 0 IcBO 10 Emitter cutoff current IEBO VEB = 5.0 V, Ic = 0 IcBO 17 DC current gain hFE1 VcE = 2.0 V, Ic = 5.0 A 450 800 2,000 DC current gain hFE2 VcE = 2.0 V, Ic = 10 A 150 IcBO 0.25 Collector saturation voltage VcE(sat)1 Ic = 5.0 A, IB = 100 mA 0.12 0.3 Collector saturation voltage VcE(sat)2 Ic = 5.0 A, IB = 50 mA 0.12 0.3 Collector saturation voltage VcE(sat)2 Ic = 10 A, IB = 200 mA 0.4 0.4 Collector saturation voltage VcE(sat)3 Ic = 10 A, IB = 100 mA 0.12 0.3 Collector saturation voltage VcE(sat)4 Ic = 10 A, IB = 100 mA Ic = 10.4 0.4 Collector capacitance VcB(sat)4 Ic = 10 A, IB = 100 mA Ic = 10.4 Ic =</td></td<>	Collector cutoff current IcBO VcB = 100 V, IE = 0 IcBO 10 Emitter cutoff current IEBO VEB = 5.0 V, Ic = 0 IcBO 17 DC current gain hFE1 VcE = 2.0 V, Ic = 5.0 A 450 800 2,000 DC current gain hFE2 VcE = 2.0 V, Ic = 10 A 150 IcBO 0.25 Collector saturation voltage VcE(sat)1 Ic = 5.0 A, IB = 100 mA 0.12 0.3 Collector saturation voltage VcE(sat)2 Ic = 5.0 A, IB = 50 mA 0.12 0.3 Collector saturation voltage VcE(sat)2 Ic = 10 A, IB = 200 mA 0.4 0.4 Collector saturation voltage VcE(sat)3 Ic = 10 A, IB = 100 mA 0.12 0.3 Collector saturation voltage VcE(sat)4 Ic = 10 A, IB = 100 mA Ic = 10.4 0.4 Collector capacitance VcB(sat)4 Ic = 10 A, IB = 100 mA Ic = 10.4 Ic =

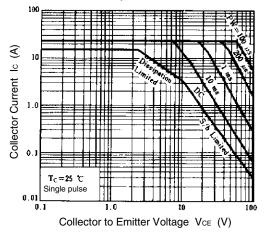
SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



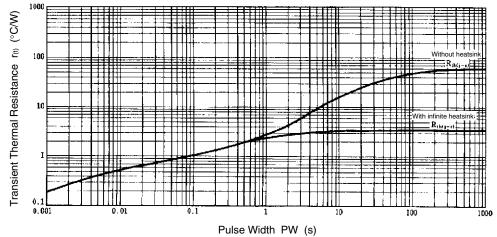
TYPICAL CHARACTERISTICS (Ta = 25°C)

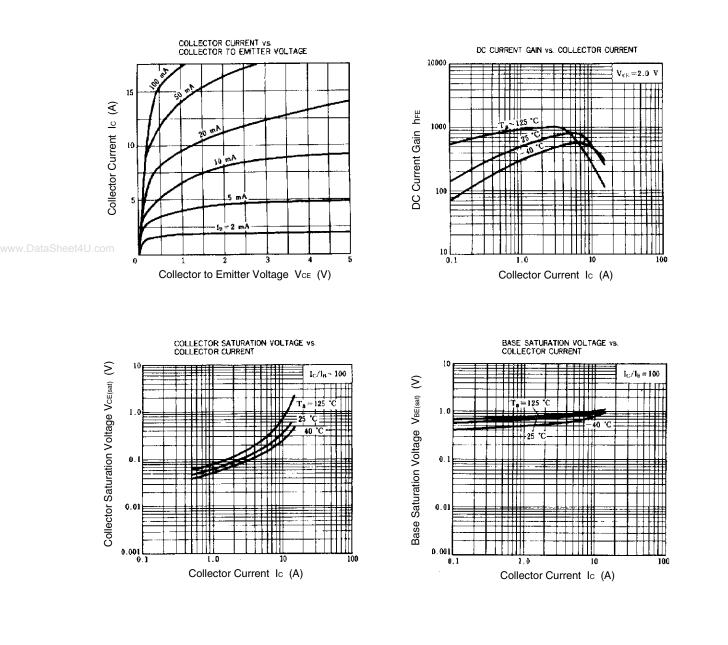


FORWARD BIAS SAFE OPERATING AREA









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